

2008 Test and Test Equipment

July 2008

San Francisco, USA

Roger Barth - Chair

ITRS Test TWG



2008 Test TWG Members

44 members – 30 Affiliations

<u>Name</u>	<u>Affiliation</u>
Dave Armstrong	Advantest
Paul Roddy	Advantest
Mike Peng Li	Altera
Mike Bienek	AMD
Amit Majumdar	AMD
Calvin Cheung	ASE
Rob Aitken	ARM
Mouli Chandramouli	ARM
Atul Goel	Avago Technologies
Tetsuo Tada	Bunri University, Japan
Steve Payne	Credence
Jack Courtney	IBM
Shawn Fetterolf	IBM
Anne Gattiker	IBM
Phil Nigh	IBM
Jody Van Horn	IBM
Dennis Conti	IBM
Peter Muhmenthaler	Infineon
Phil Burlison	Inovys
Wendy Chen	KYEC
David Wu	Intel
Koorosh Zaerpoor	Intel

<u>Name</u>	<u>Affiliation</u>
Yi Cai	LSI
Jerry McBride	Micron
Peter Maxwell	Micron
Roger Barth	Numonyx - Chair
Bill Price	NXP Semiconductors
Rene Segers	NXP Semiconductors
Wataru Uchida	Renesas (STRJ)
Sejang Oh	Samsung
Davide Appello	STMicroelectronics
Sridhar Kannan	Stream Processors
Prasad Mantri	Sun Microsystems
Tom Williams	Synopsys
Brad Robbins	Teradyne
Lee Song	Teradyne
Steve Comen	TI
Shichi Ito	Toshiba (STRJ)
Ulrich Schoettmer	Verigy
Erik Volkerink	Verigy
Yervant Zorian	Virage Logic
Mike Rodgers	Consultant
John Lukez	Consultant



2008 Test Updates

- Mixed Signal
 - mid & max ranges vs. high only
 - Waveform generators – 40-80 MHz mid vs 120-320 MHz max
 - Noise floor at -145dB for mid vs. -165dB for max
 - Non-numerical changes to reflect current state of the art
- RF
 - Faster Radio adoption rate and RF ports per device
 - Non-Numerical changes to table to reflect current state of the art
- Logic
 - Likely minor revision in logic data volumes
 - SoC DFT wrapper alignment with between design and test
- Memory
 - 200 MHz NAND updated to reflect ONFI-2 performance pull-in
 - LPDDR2 performance will be added in the 2009 roadmap



Challenges



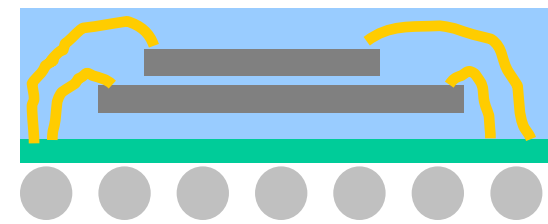
Challenge - DFT

- Encompassing “More than Moore”
 - Multi-heterogeneous core devices
- Rewrite with partitioning between design and test chapters
 - Test – requirements for low cost
 - Design – implementation methodology
- Test power vs. operational power management
- Test wrappers for future cores
 - Method to handle legacy cores
- Scalable DFT architecture – die to system operation
- Compression, compression ratio and fault isolation

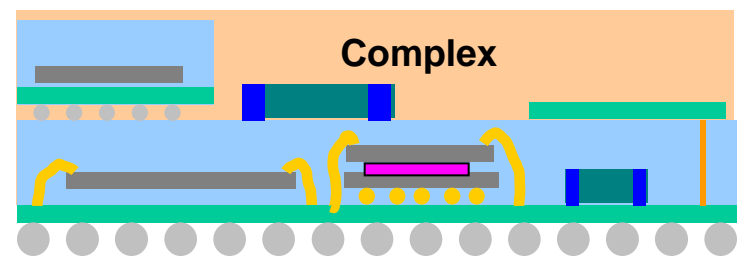
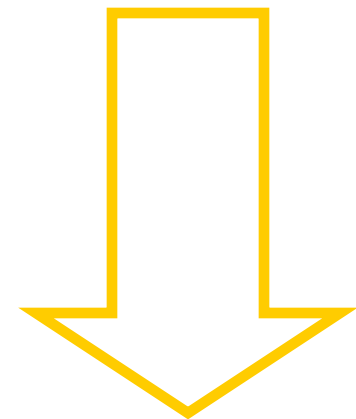


Challenge – SiP Test

- Now highly complex systems
 - Any Silicon (digital, analog) & passives
 - Packaged ICs, other SiP
- Targets consumer & low power
- Challenges
 - High yield with low test cost
 - Standardized test strategy
- Potential solutions
 - Design for die, debug and system test
 - Per die BIST and accessibility at all levels
 - KGD use with minimal post test
 - On-SiP test engine



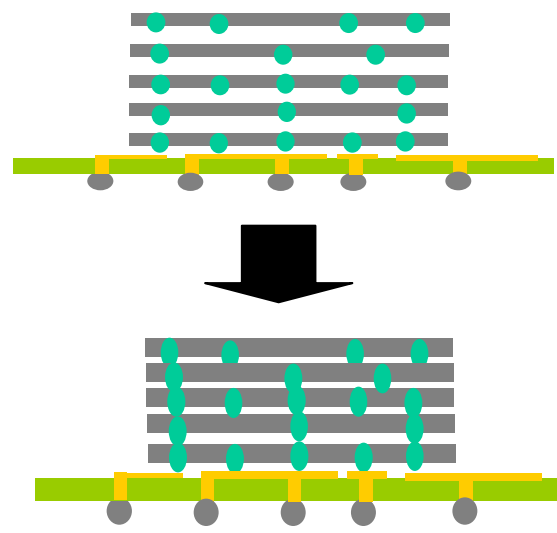
Simple



Complex

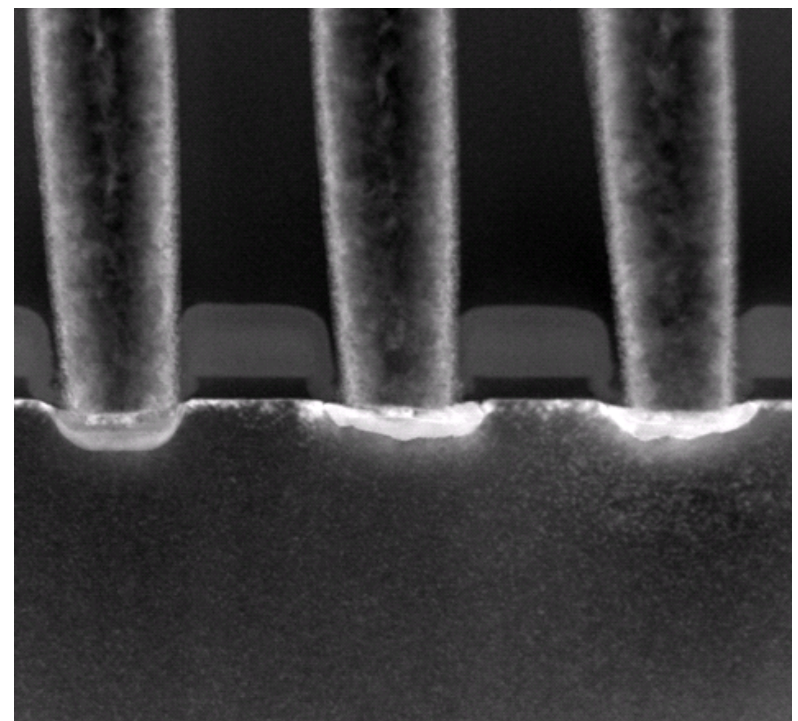
Challenge - 3D Devices

- Multiple die system
 - Sub-systems designed to be assembled together
 - Connection is by potentially 1000's of TSVs (Thru Silicon Via's)
- Design, Test and Assembly joint problem
- Requirements
 - Testability of each die
 - Via continuity checks - for signal and non-signal vias
 - Cross die test methodology
 - System (die stack) test post assembly
 - Multi-die domain EDA tools required



Challenge: Test for Yield Learning

- “Visualize” Non-visible defects...yield learning is statistical!
 - Predominant in roadmap
 - “Feature” of approaching the wall
- Smart Data Mining tools
 - Find common signatures in fail data
 - Adaptive data collection
- Localization of defects



Challenge – Cost of Test

- Maintain Moore's Law learning per technology
- Effective use of DFT die size budget per litho
- Make the device appear "smaller"
 - Concurrent test of similar structures or cores
 - Memory folding and compression
- Higher parallelism on reduced pin interfaces
- Self Test
- Reuse of older tools
- Guaranteed "performance" by proving "functionality"



Challenge - Mechanical Handling

- Small ball pitches on high parallelism memory (>0.4mm)
- Very small packages (2mm x 3mm)
- Testing and handling of < 20um “thin” die
- High test parallelism
- 450mm wafers



Challenge - Fault Tolerant Devices

“Bad but Good”

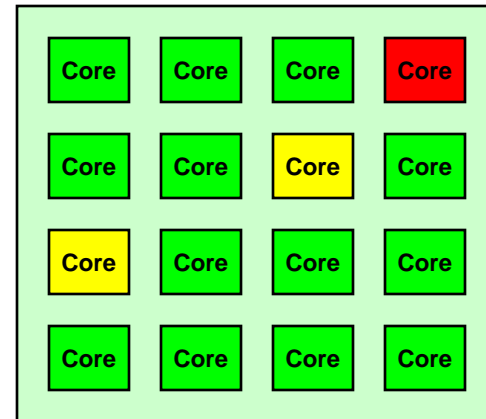
- Multiple identical core MPUs...not all cores need be good
- Memory with allowable bad bits / blocks
- Image sensors without the “perfect” image



Challenge: Fault Tolerant Device

“Bad but Good”

- Multi identical core MPU
- Core issues
 - 1 bad
 - 2 marginal
- Is MPU good or bad?
 - Disable cores?
 - Fix or “Ignore” with smart OS kernel?

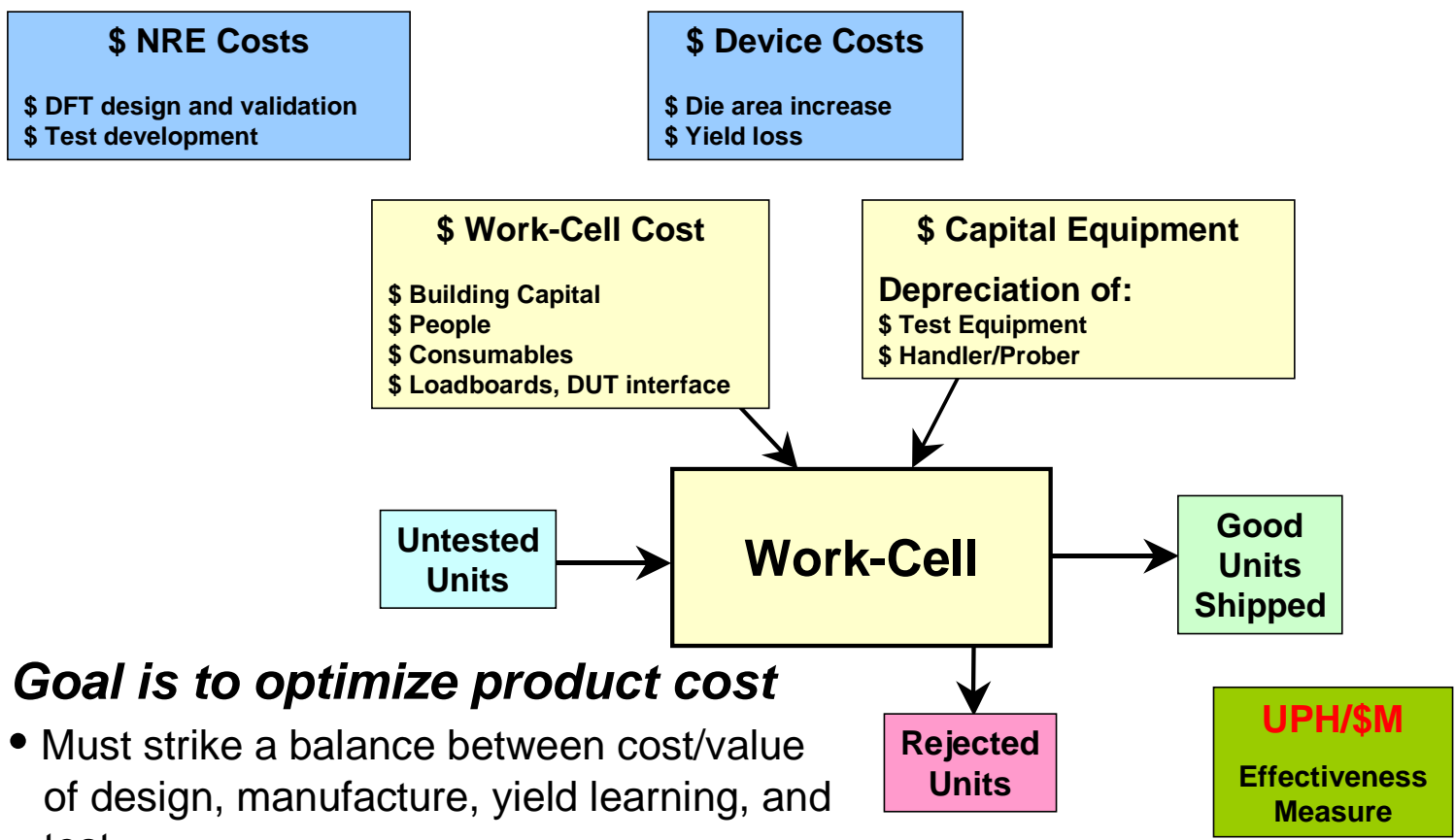


2008 Key Drivers

- Device trends
 - Increasing device interface **bandwidth** (# of signals and data rates)
 - Increasing **device integration** (SoC, SiP, MCP, 3D packaging)
 - Integration of emerging and **non-digital CMOS** technologies
 - **Complex package** electrical and mechanical characteristics
 - Device **characteristics beyond** one sided **stimulus/response** model
 - **Multiple I/O types and power supplies on same device**
- Increasing test process complexity
 - Device **customization** during the test process
 - “**Distributed test**” to maintain cost scaling
 - **Feedback** data for tuning manufacturing
 - **Dynamic test flows via “Adaptive Test”**
 - Higher order dimensionality of test conditions
- Continued economic scaling of test
 - **Physical limits** of test parallelism
 - Managing (logic) test data and feedback **data volume**
 - Effective limit for speed difference of **HVM ATE versus DUT**
 - Managing **interface hardware** and (test) socket costs
 - Trade-off between the **cost of test** and the **cost of quality**
 - **System test and BIST** driving multiple test socketings



Cost of Test



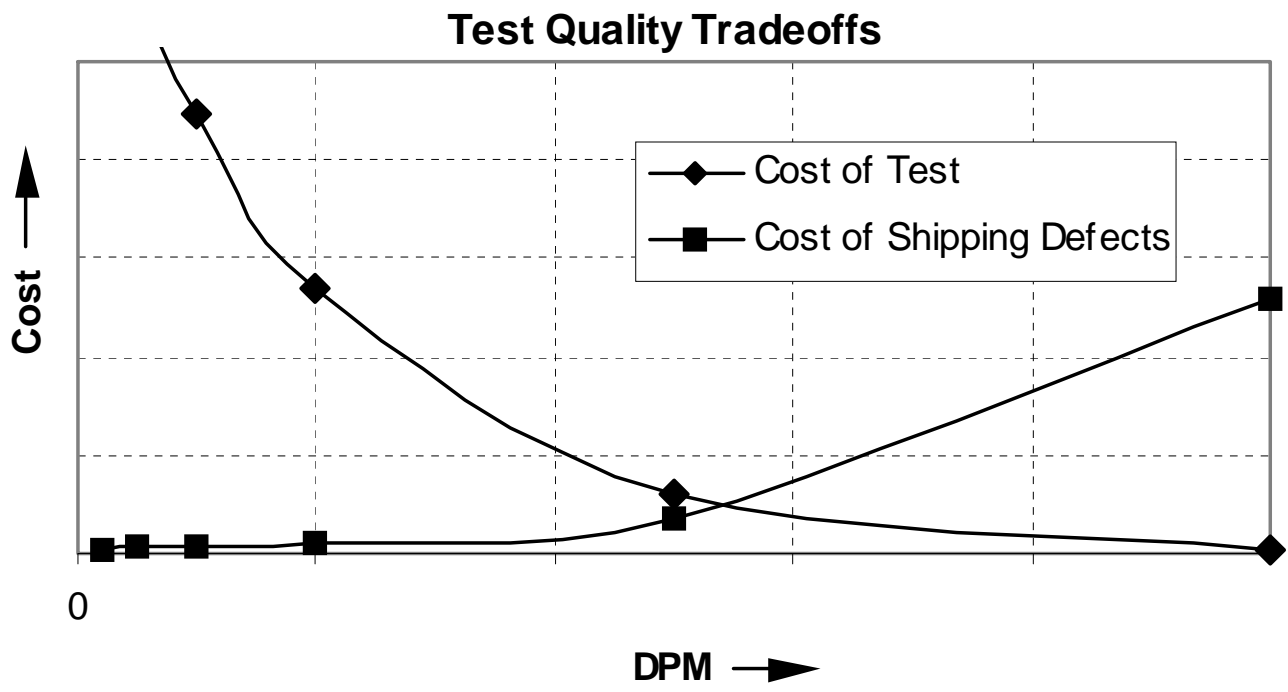
Goal is to optimize product cost

- Must strike a balance between cost/value of design, manufacture, yield learning, and test



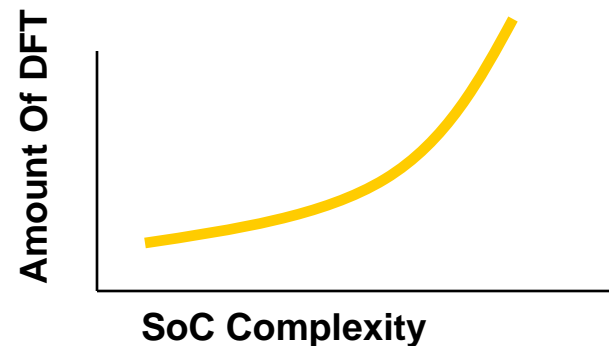
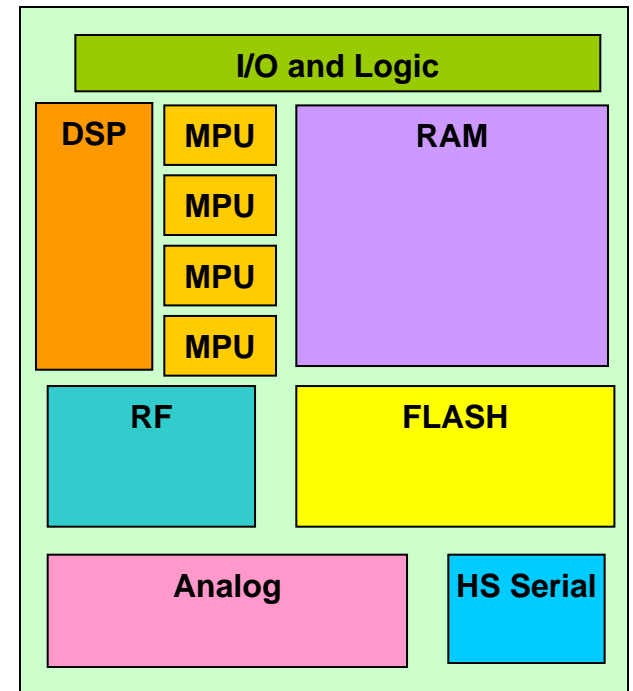
Cost of Quality

- Test is a balance of DPM and cost
- Shipped defect cost is more than bad components
 - Customer relationships, goodwill, penalties



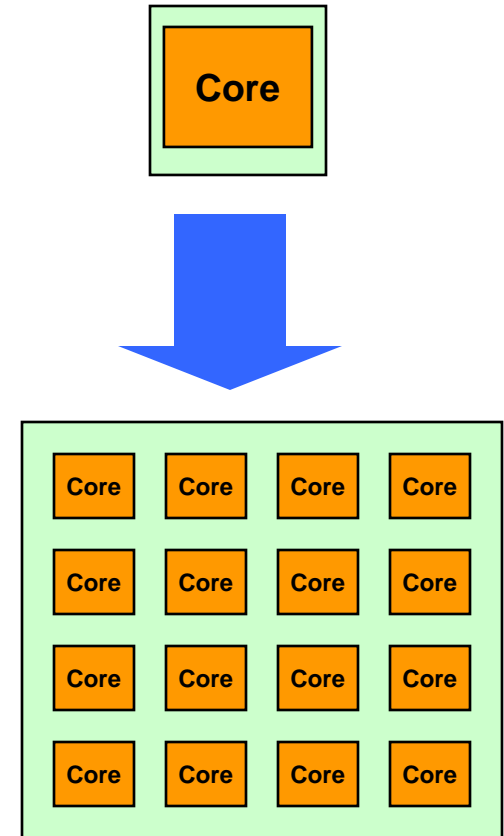
SoC – Consumer Logic

- > 1000 cores by 2020
 - MPU / logic
 - Memory
 - Analog / RF
 - HS serial
- Per core DFT
- SoC test challenges
 - Management of per core DFT
 - Standardization of core “wrappers”
 - IEEE 1500 core test
 - IEEE P1687 JTAG chip-test

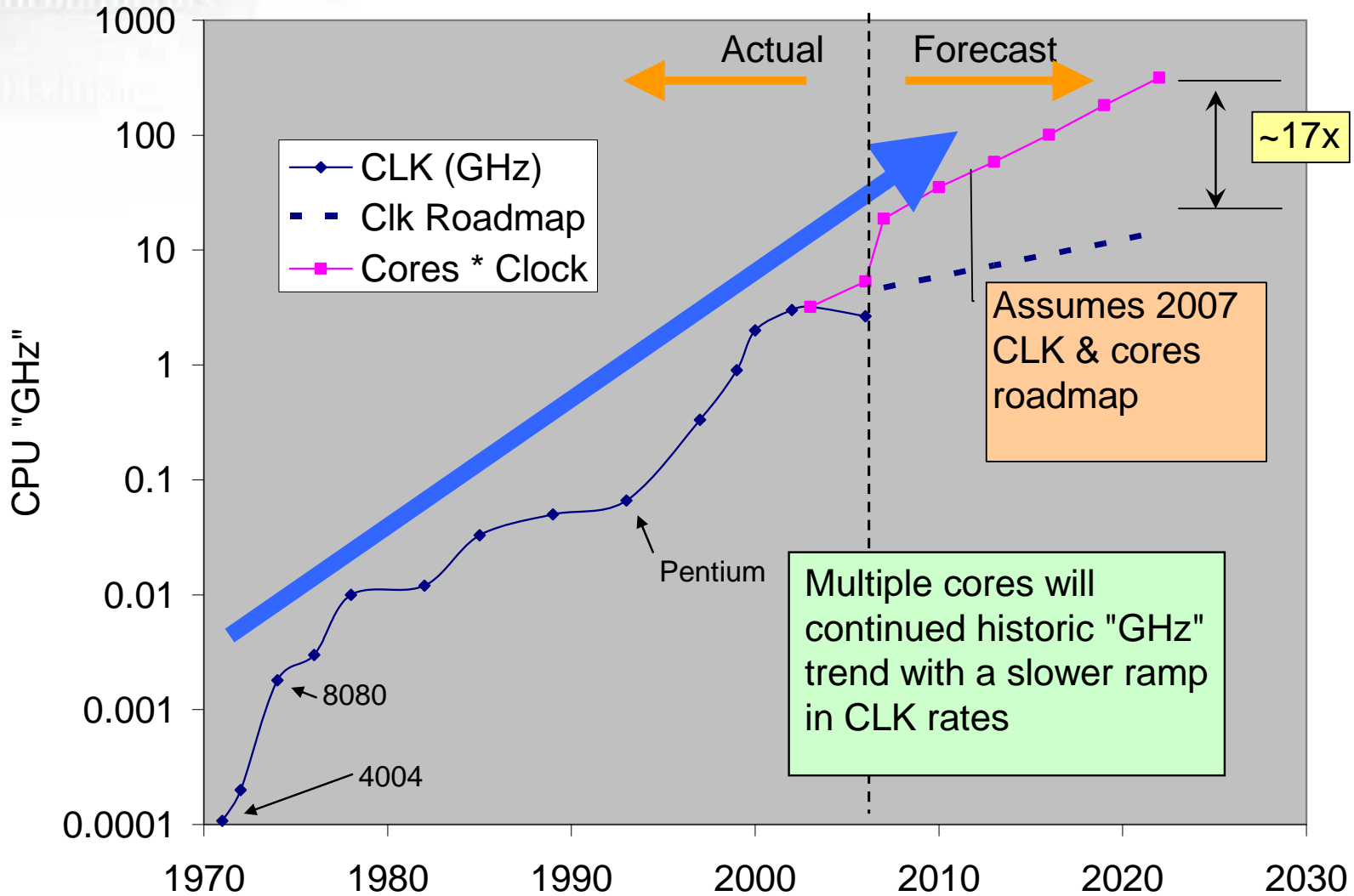


High End Logic

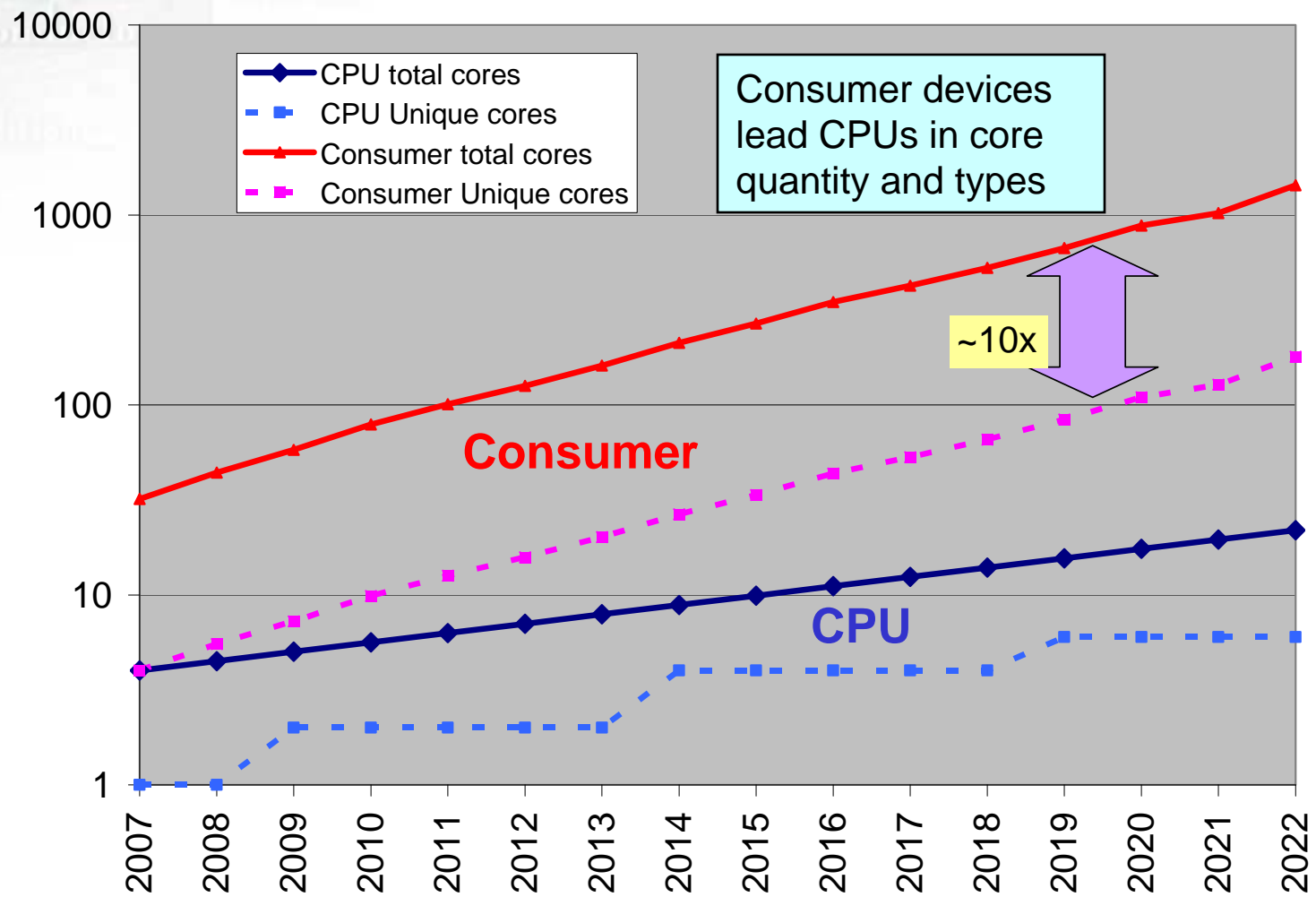
- Trend: Single to Multi core
 - Forecast: 22 cores by 2020
- I/O GT/s increasing
 - Aligned to number of cores
 - Multi-lane HS serial to 20GT/s
- Non-diff I/O will remain below 2 GT/s
 - Accuracy and noise limitations
- Structural test at low speed
 - Vectors increasing with Flip-Flop count



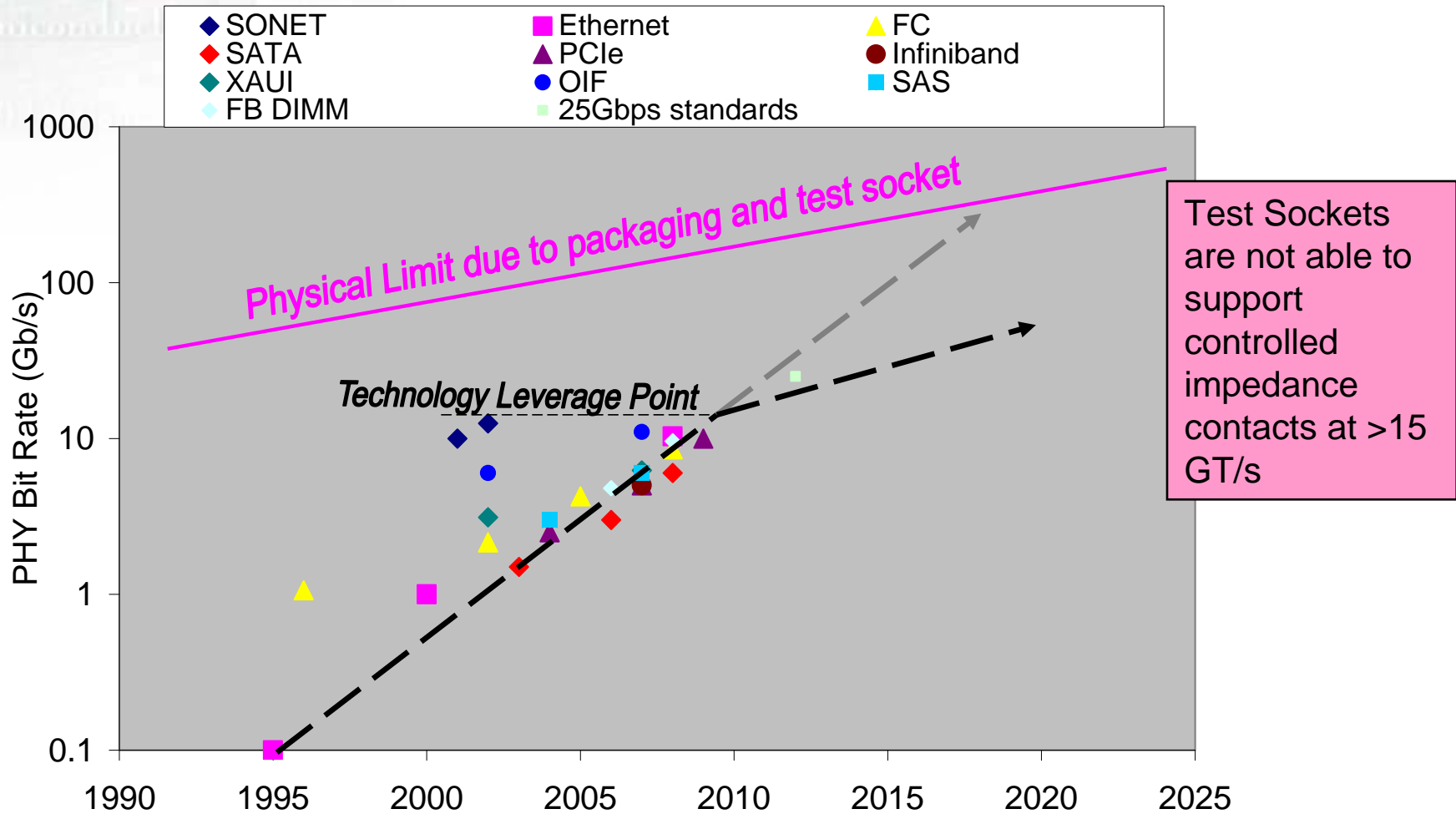
MPU "GHz" by "Cores"



Proliferation of Cores



High Speed Interfaces

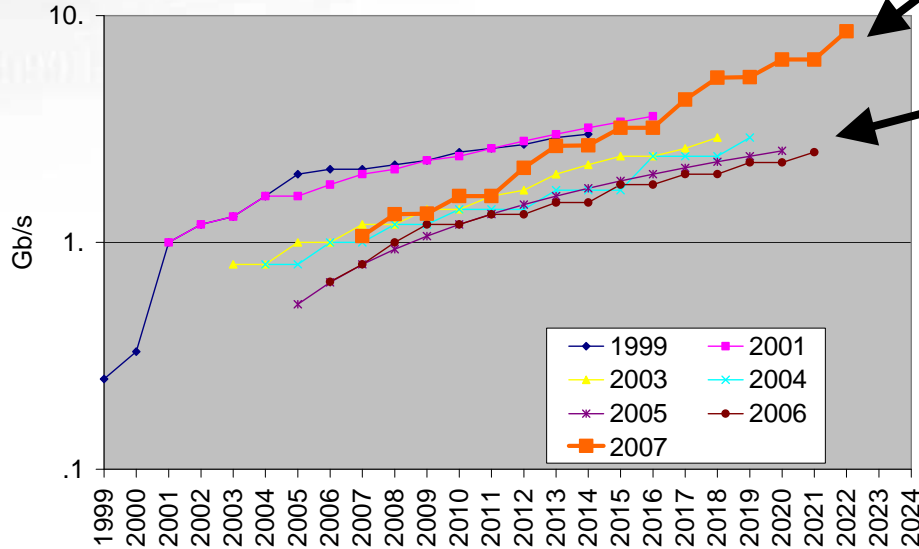


- Bit bandwidth increasing – Physical limit? Test limit?



DRAM Model

DRAM I/O Rate



2007 DDR model removed previous fcst I/O rate "flatness"

DDR4 thru DDR6 roadmaps are pure speculation

- DDRx family trends
 - 3 primary bit rates + two optional
 - Intro year → First two speeds
- DDRx to DDRy cycles
 - 2000→2007 - 3 years
 - 2007+ - 5 years

	single I/O MegaTransitions per second							
	Clk	SDR	DDR	DDR2	DDR3	DDR4	DDR5	DDR6
1997	133	133						
1998	133	133						
1999	166	166						
2000	166	166	266 333					
2001	200		400					
2002	200		400					
2003	266			400 533				
2004	333			666				
2005	333			666				
2006	400			800				
2007	533				800 1066			
2008	666				1333			
2009	666				1333			
2010	800				1600			
2011	800				1600			
2012	1066					1600 2133		
2013	1333					2666		
2014	1333					2666		
2015	1600					3200		
2016	1600					3200		
2017	2133						3200 4266	
2018	2666						5333	
2019	2666						5333	
2020	3200						6400	
2021	3200						6400	
2022	4266							6400 6532



RF

0.8 GHz					2 GHz		5 GHz		10 GHz		28 GHz		77 GHz		94 GHz	
GSM	PDC	DCS	WLAN	SAT TV	WLAN	SAT TV	LMDS	AUTO	All Weather							
CDMA	GPS	PCS	802.11b/g		802.11a	WLAN	WLAN	Radar	Landing							
ISM		DECT	Bluetooth			Hyperlink										
	SAT Radio	CDMA	ZigBee			UWB										

Year of Production	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022
Carrier Frequency (GHz) Leading edge	18	18	22	22	60	77	77	95	95	95	95	95	95	95	95	95
Carrier Frequency (GHz) High Volume	6	8	12	12	22	22	36	36	36	36	36	36	36	36	36	36
Modulation RF BW (MHz) Leading edge	80	528	528	528	528	528	528	528	528	528	528	528	1000	1000	1000	1000
Modulation RF BW (MHz) High Volume	20	40	80	528	528	528	528	528	528	528	528	528	528	528	1000	1000
Amplitude Accuracy (dB)	<0.8	<0.6	<0.5	<0.5	<0.5	<0.25	<0.25	<0.25	<0.25	<0.25	<0.25	<0.25	<0.125	<0.125	<0.125	<0.125
ACLR (dB)	65	65	70	72	72	72	75	75	80	80	80	85	85	85	85	85
Number of RF Ports per Device	<9	<12	<16	<20	<24	<20	<18	<16	<16	<16	<16	<16	<16	<16	<16	<16
Phase Noise (dBc/Hz @ 100k offset)	-125	-130	-135	-140	-142	-145	-148	-150	-150	-150	-152	-152	-152	-152	-152	-152
Error Vector Magnitude 3G/4G	1-2%	1-2%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%	0.5%
OIP3 (dBm)	30	30	30	30	30	30	30	30	30	30	30	30	30	30	30	30
IIP3 (dBm)	40	50	60	60	60	60	60	60	60	60	60	60	60	60	60	60

- High Frequency RF is characterized and sample tested
- >50 GHz testing is a roadblock



DUT Interface

- Probe
 - Wide range of test parallelism
 - High end logic – x1
 - NAND – Full wafer
 - Pad size requirements based on probing area & temp range
 - KGD performance test difficult – interface effects
- Sockets
 - Tables added for 2007
 - TSOP – Flash (NAND) – Contact blade
 - BGA – DRAM – Spring Probe
 - BGA – SoC – Spring Probe (50 ohm)
 - BGA – SoC – Conductive Rubber
 - Test limitations for pitch below 0.5mm and frequency > 30GHz

Specialty Devices

- LCD drivers
 - Form factor of 30mm x 1.5mm
 - Long bond pads on 20um centers
- Image sensors
 - Micro lens check with pupil test
- 3 axis MEMS Accelerometer
 - Consumer drop/rotate applications

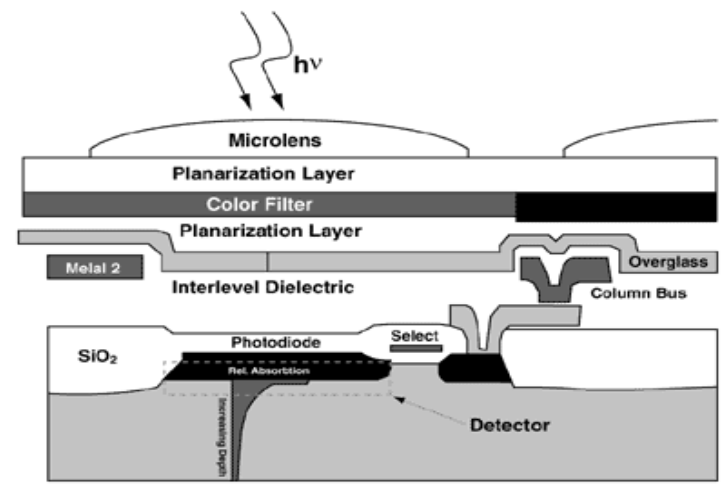
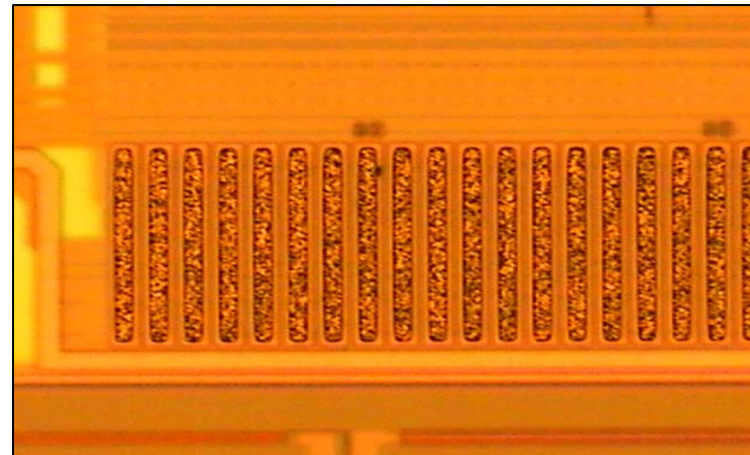


Image sensor structure cross section²⁴



Test Roadmap Issues for 2008-2009

- DFT
 - Models going forward
- More than Moore test model
 - SoC, SiP
- Test Cost
- Memory
 - Very high speed differential bus – Protocol based?
- I/O bandwidth
 - Test driven walls
- Adaptive Test



2008 Plans

- Table update only
- Plan 2009 changes
 - DFT alignment with design TWG
 - Socket performance vs. frequency
 - Expansion of specialty devices
 - Adaptive Test
 - SiP & 3D silicon Test

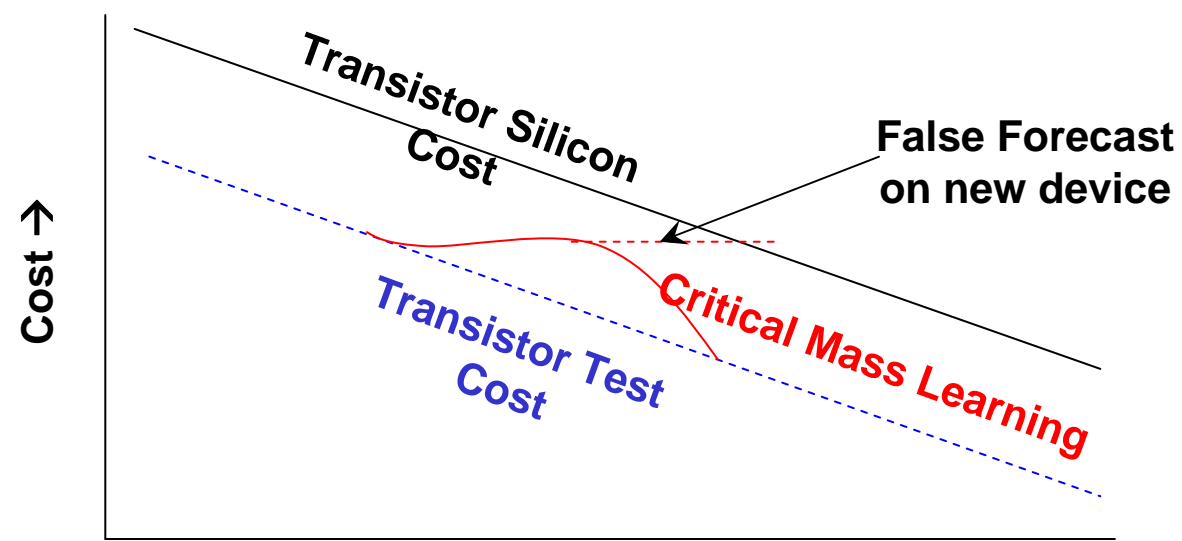


Backup

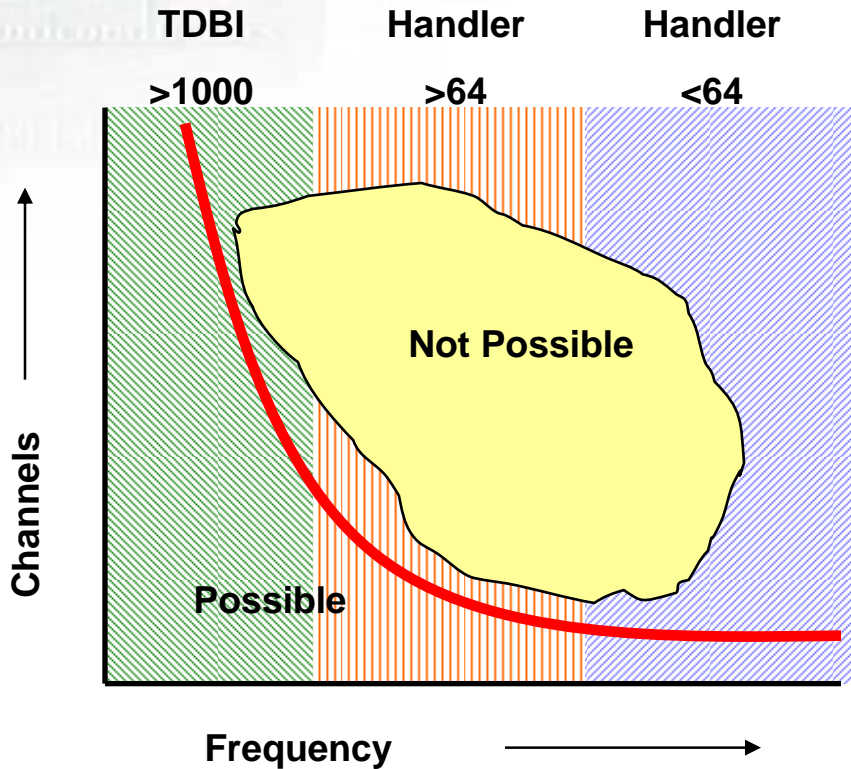


Challenge: Cost Trend

- Maintain Moore's Law learning
 - Deviations are a call to action - i.e. Functional to Structural test
- Learning curve lag on new devices, integrations or architectures
 - Low cost test methods require critical mass learning

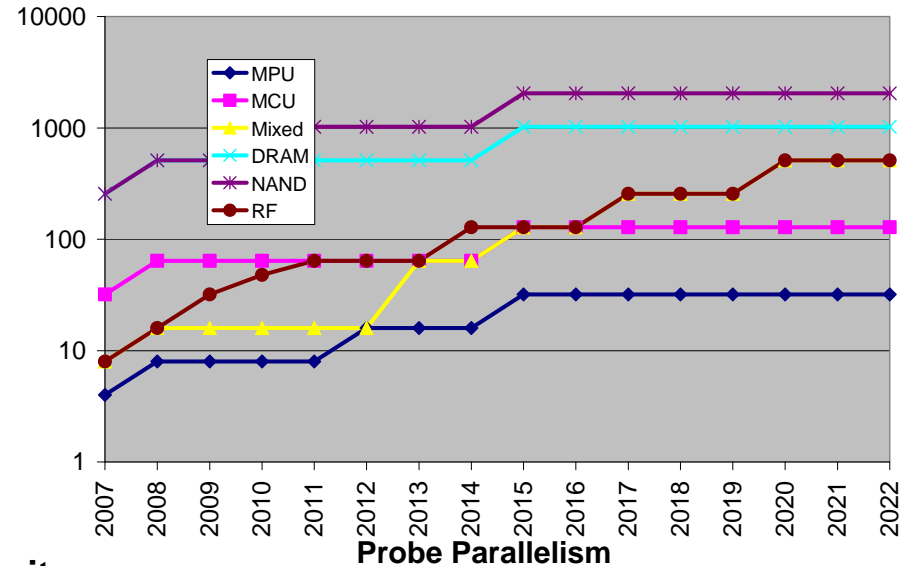


Challenge: Limits to test parallelism

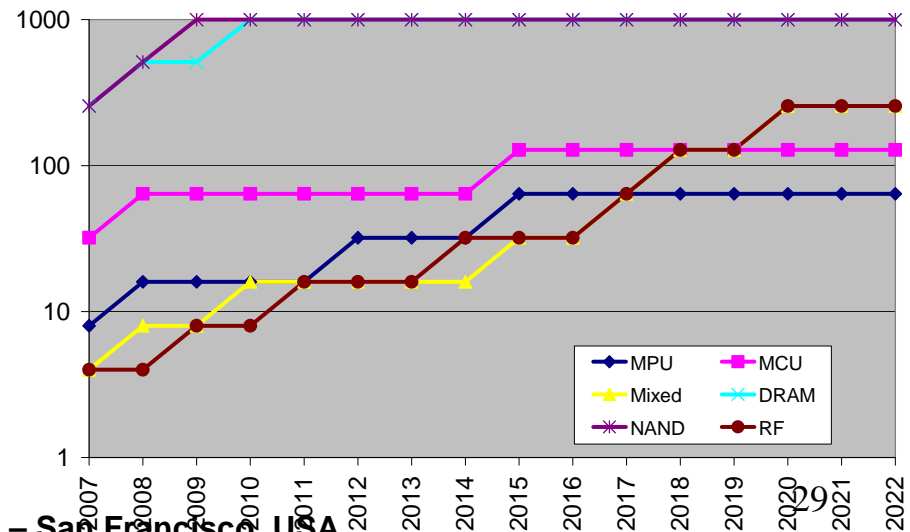


- Low Frequency: Mechanical - Cables and connections
- High Frequency: Electrical - Signal integrity
- Parallelism is a function of test time

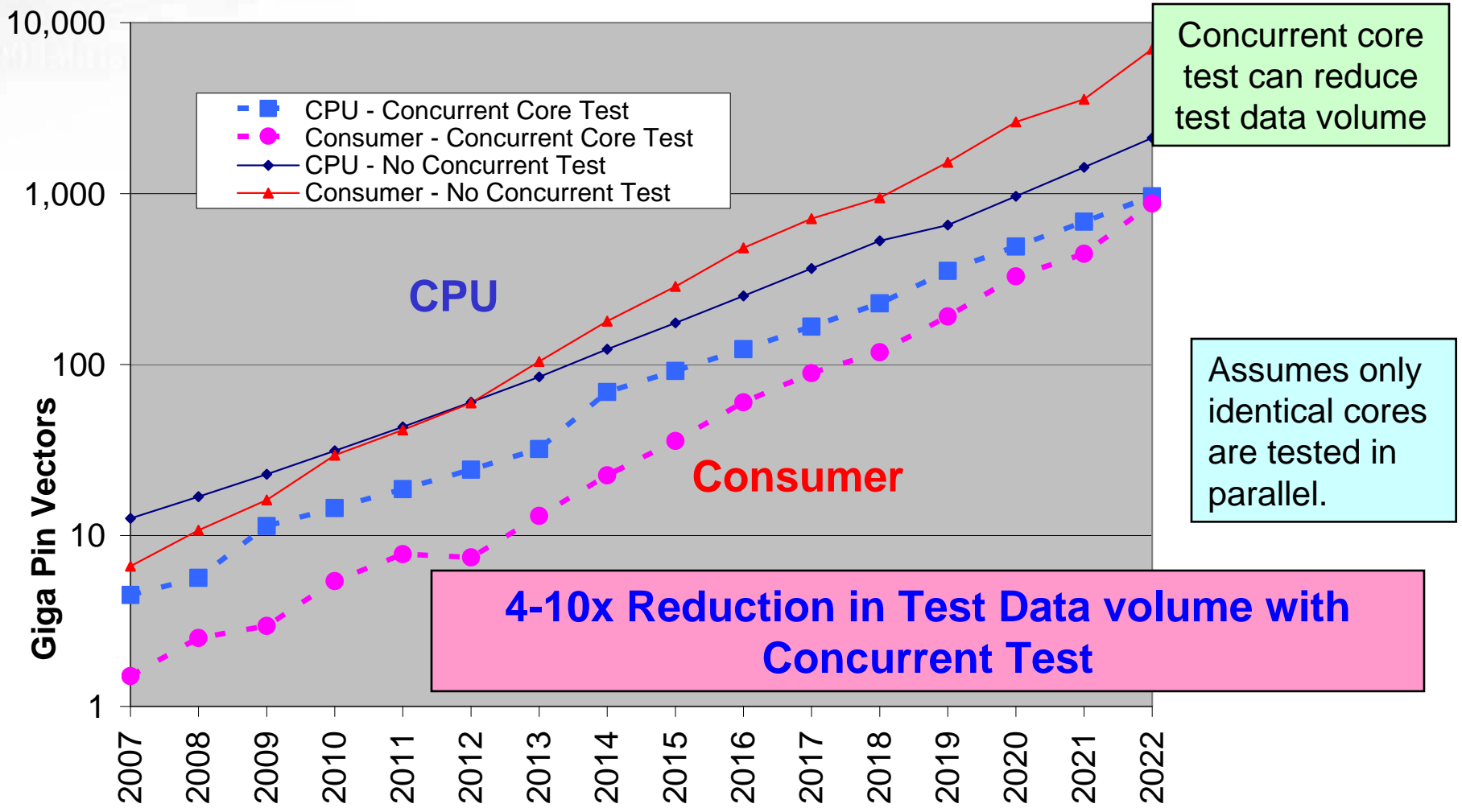
Packaged Test Parallelism



Limit



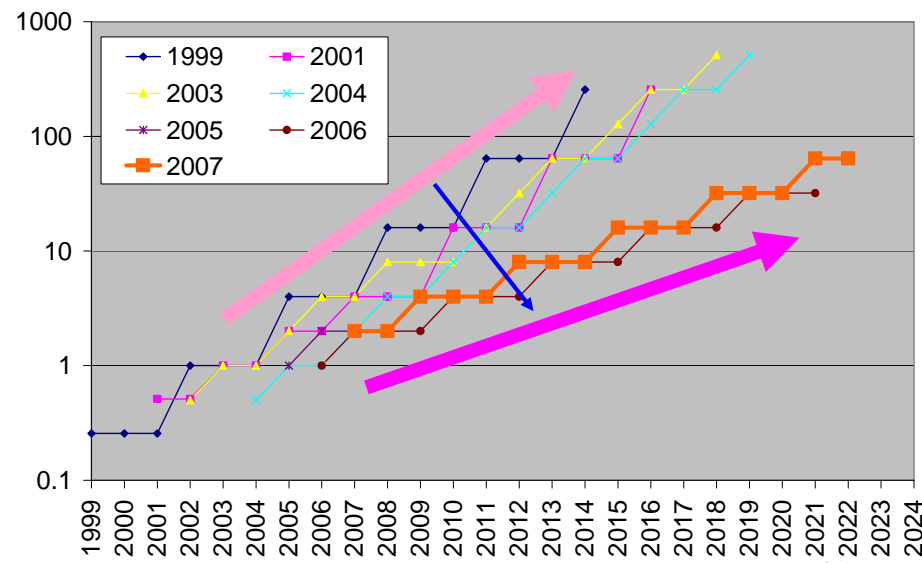
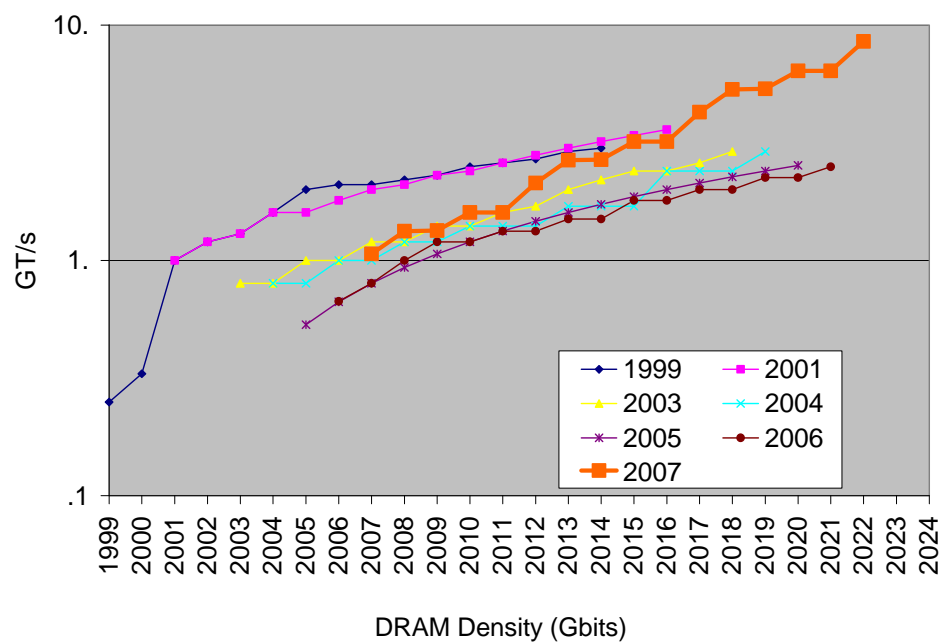
Digital Logic Test Data Volume



DRAM Trends

vs. Fcst

- Speculative beyond DDR3
- Cell size remains $6F^2$
- Increased I/O rate in 2007 to support revised DDR4→DDR6 model
- Density aligned to litho roadmap



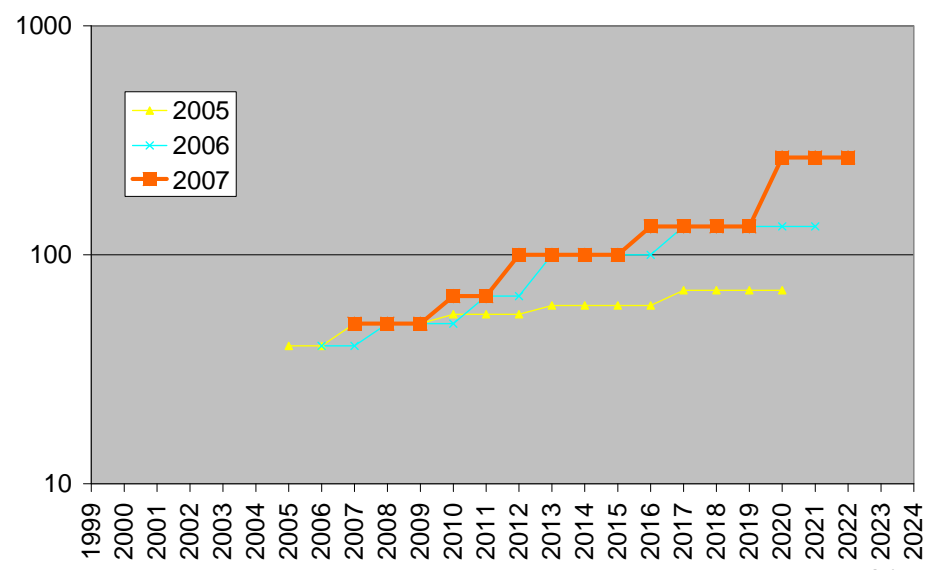
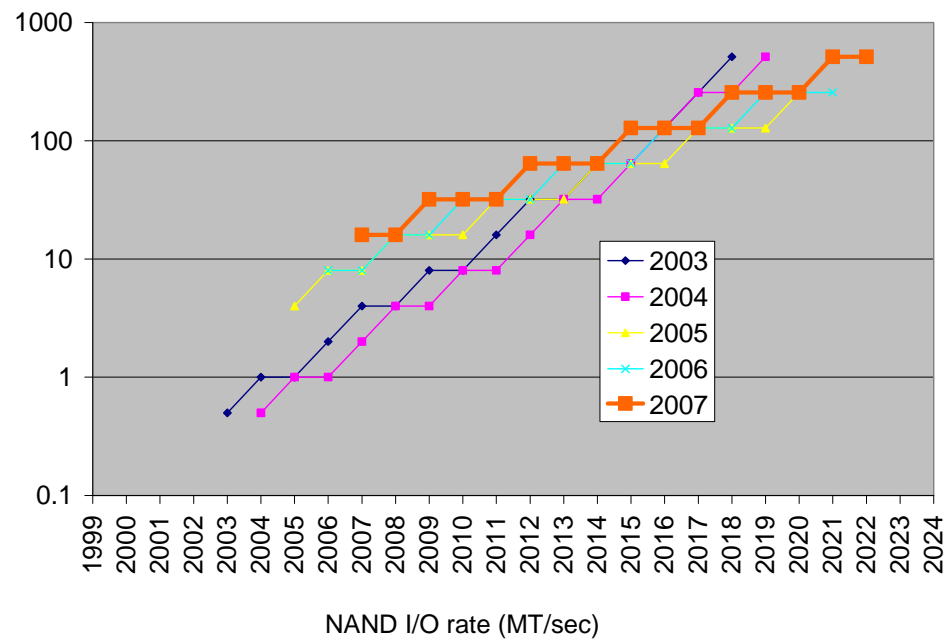
NAND Trends

vs. Fcst

- Density growth has flattened slightly
 - 4F² Cell size (SBC)
 - 3 year Litho trend
 - 2 B/C assumed

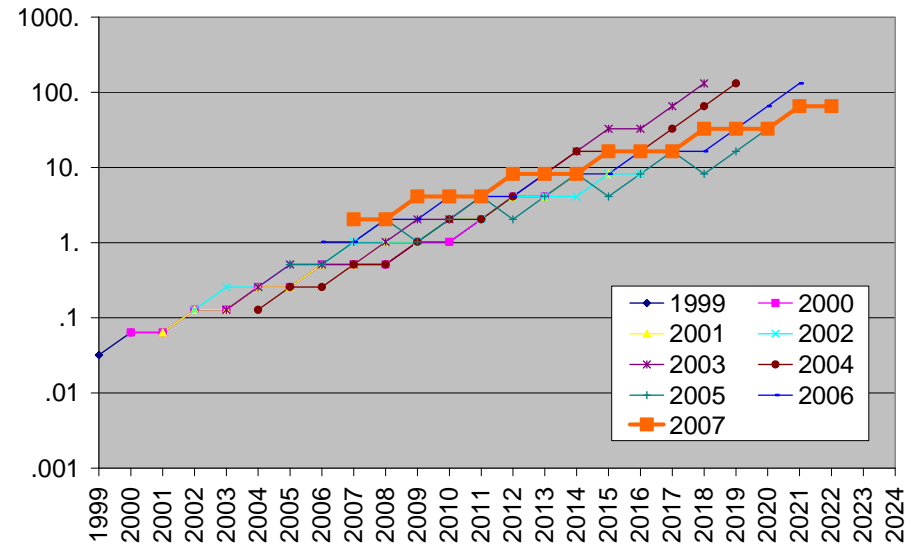
- I/O MT/s W/R rate driven

- ONFI spec
 - DDR
 - Block Abstraction
 - Common command set

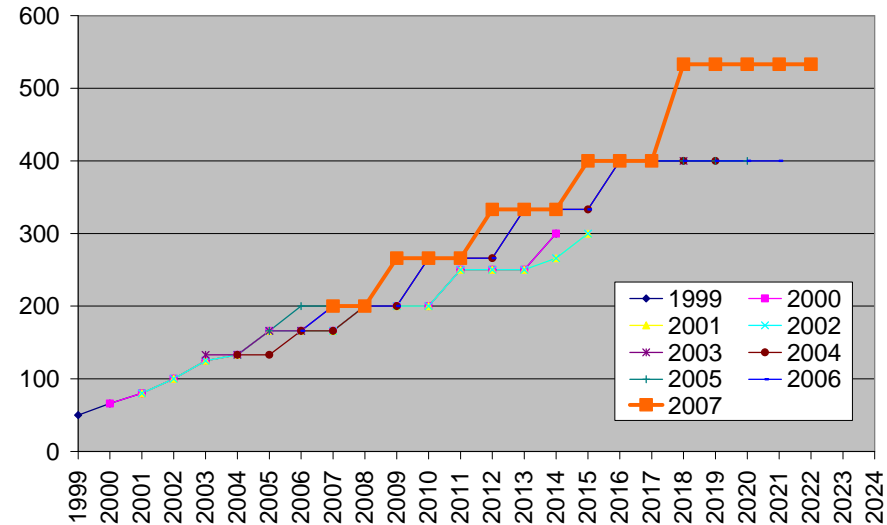


NOR Trends vs Forecasts

- I/O rate scaling to Cellular requirements
- Density roadmap well known
 - MLC prior to 1999
- X32 data has not appeared
 - Dropped from forecast

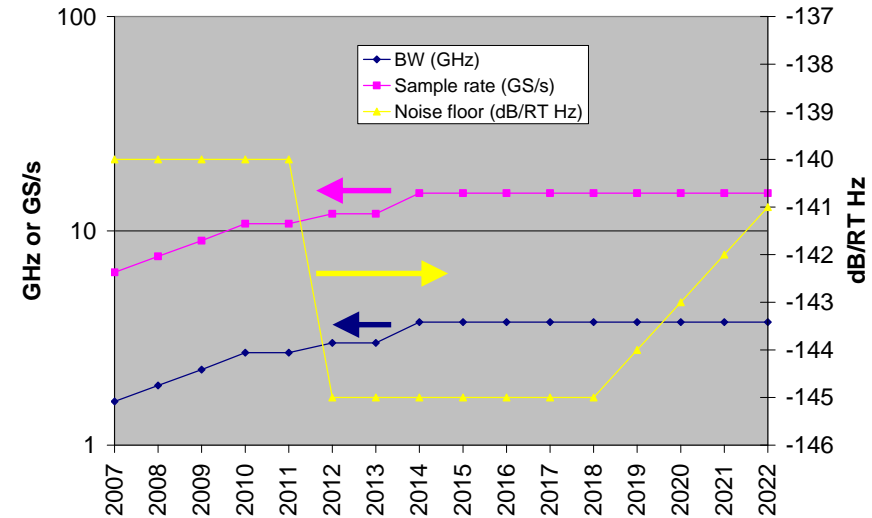


NOR I/O rate (MT/s)



Mixed Signal

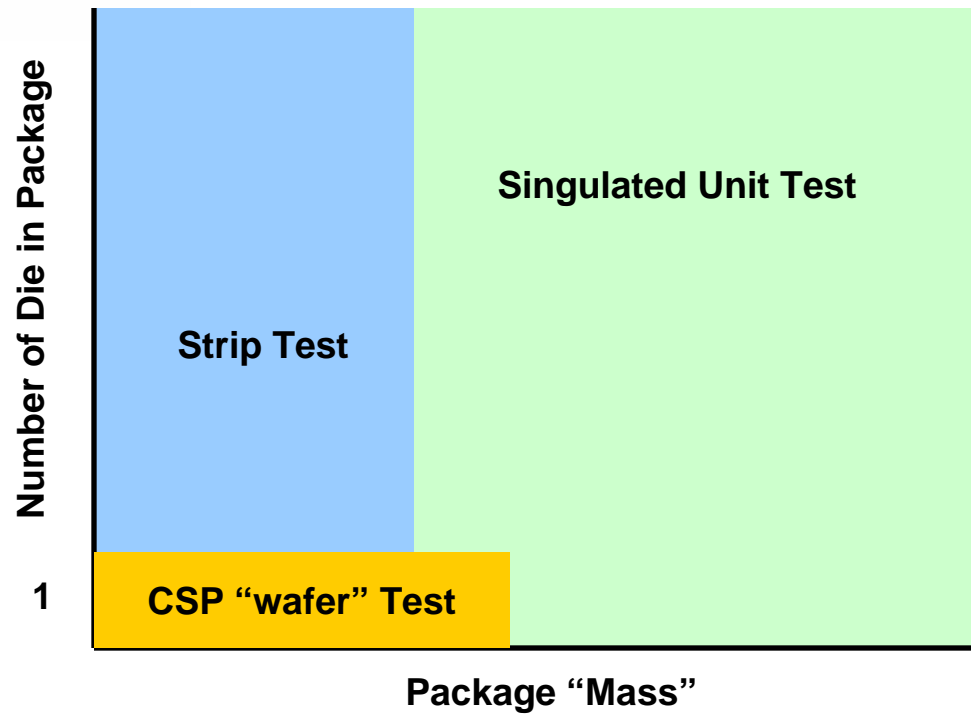
- Small changes from 2005
 - Noise floor flattened
 - Sampling rate increased



	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022
<i>Low Frequency Waveform</i>																
BW (MHz)	50	75	75	75	100	100	100	100	100	100	100	100	100	100	100	100
Sample rate (MS/s)	Moving from Nyquist sample rates to over/under sampling sources/digitizers															
Resolution (bits)	DSP computation to 24 bits, effective number of bits limited by noise floor															
Noise floor (dB/RT Hz)	-155	-160	-160	-160	-165	-165	-165	-165	-165	-165	-165	-165	-165	-165	-165	-165
<i>Very High Frequency Waveform Source</i>																
Level V (pk-pk)	4	4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4
Accuracy (±)	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%
BW (GHz)	1.6	1.9	2.25	2.7	2.7	3	3	3.75	3.75	3.75	3.75	3.75	3.75	3.75	3.75	3.75
Sample rate (GS/s)	6.4	7.6	9	10.8	11	12	12	15	15	15	15	15	15	15	15	15
Resolution (bits) AWG/Sine†	8/10	8/10	8/10	8/10	8/10	10/12	10/12	10/12	10/12	10/12	10/12	10/12	10/12	10/12	10/13	10/14
Noise floor (dB/RT Hz)	-140	-140	-140	-140	-140	-145	-145	-145	-145	-145	-145	-145	-145	-145	-145	-145
<i>Very High Frequency Waveform Digitizer</i>																
Level V (pk-pk)	4	4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4	<4
Accuracy (±)	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%	0.50%
BW (GHz) (under sampled)	9.2	10.8	10.8	12.5	12.5	15	15	15	15	15	15	15	15	15	15	15
Sample rate (GS/s)	0.4	0.4	0.4	0.4	0.4	0.6	0.6	0.6	0.6	0.6	0.6	0.6	0.6	0.6	0.6	0.6
Min resolution (bits)	12	12	12	12	12	14	14	14	14	14	14	14	14	14	14	14
Noise floor (dB/RT Hz)	-145	-145	-145	-145	-145	-150	-150	-150	-150	-150	-150	-150	-150	-150	-150	-150
<i>Time Measurement</i>																
Jitter measurement (ps RMS)	Will be driven by high-speed serial communication ports								Will be driven by high-speed serial communication ports							
Frequency measurement (MHz)	Will be driven by high-performance ASIC clock rates								Will be driven by high-performance ASIC clock rates							
Single shot time capability (ps)	Will be driven by high-speed serial communication ports								Will be driven by high-speed serial communication ports							



Package Size & Test



Package roadmap supports 0.2mm thickness

Singulated Unit test appears to have limits based on mass

Mechanical

- Single Prober Roadmap
 - 450mm wafers assumed in 2014

Year of Production	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022
Wafer diameter (mm)	300	300	300	300	300	300	300	450	450	450	450	450	450	450	450	450
Wafer thickness (um)	80-775	80-775	80-775	80-775	80-775	80-775	80-775	50-1000	50-1000	50-1000	50-1000	50-1000	50-1000	50-1000	50-1000	50-1000
Maximum I/O pads	3000	4000	4000	5300	5300	5300	5300	5300	5300	5300	5300	5300	5300	5300	5300	5300
Chuck X & Y positioning accuracy (um)	2	2	1	1	1	1	1	1	1	1	1	1	1	1	1	1
Chuck Z positioning accuracy (um)	1	1	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5	0.5
Probe-to-pad alignment (um)	4.5	4.5	4.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5	3.5
Maximum chuck force (kg)	100	100	100	100	100	100	100	100	100	100	100	100	100	100	100	100
Set point range (°C)	-30 to +85	-30 to +85	-30 to +85	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125	-45 to +125
Total power (Watts)	130	130	250	250	250	250	250	250	250	250	250	250	250	250	250	250
Power density (Watt/cm ²)	60	60	120	120	120	120	120	120	120	120	120	120	120	120	120	120

- Three handler groups
 - High power - > 10W
 - Low parallelism: < 4
 - Medium Power → 0.5 to 10W
 - Medium parallelism: < 16
 - Low Power → < 0.5W (Memory, MCU, etc)
 - High parallelism: <250

